## SILICON EPITAXIAL PLANAR DIODE

## Applications

Ultra high speed switching





SOT-323 Plastic Package Marking Code: **PH** 

## Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

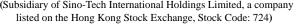
Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V <sub>RM</sub>	85	V
Reverse Voltage	V <sub>R</sub>	80	V
Average Forward Current	Ι <sub>Ο</sub>	100	mA
Maximum (Peak) Forward Current	I <sub>FM</sub>	300	mA
Peak Forward Surge Current (t <sub>p</sub> = 10 ms)	I <sub>FSM</sub>	2	А
Total Power Dissipation	P <sub>tot</sub>	200	mW
Junction Temperature	TJ	125	°C
Storage Temperature Range	Ts	- 55 to + 125	°C

## Characteristics at $T_a = 25 \ ^{\circ}C$

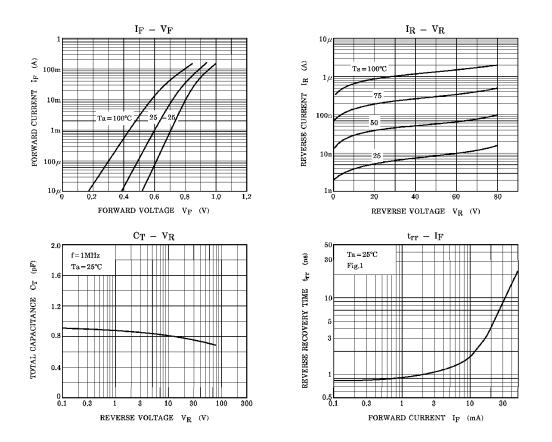
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I <sub>F</sub> = 100 mA	V <sub>F</sub>	-	1.2	V
Reverse Current at $V_R = 30 V$ at $V_R = 80 V$	I <sub>R</sub>	-	0.1 0.5	μΑ
Total Capacitance at $V_R = 0$ , f = 1 MHz	C <sub>T</sub>	-	3	pF
Reverse Recovery Time at I <sub>F</sub> = 10 mA, V <sub>R</sub> = 6 V, I <sub>rr</sub> = 1 mA, R <sub>L</sub> = 100 $\Omega$	t <sub>rr</sub>	-	4	ns















(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



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